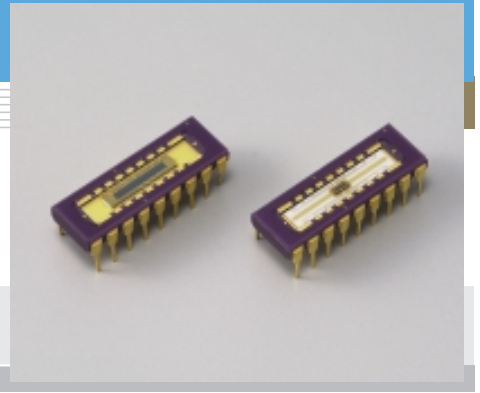


InGaAs PIN photodiode array

G7150/G7151-16

16-element array



Features

- 16-element array
- For simple measurement

Applications

- Near Infrared (NIR) spectrophotometer

General ratings

Parameter	G7150-16	G7151-16	Unit
Package	DIP		-
Active area	0.45 × 1 (× 16 elements)	0.08 × 0.2 (× 16 elements)	mm

Absolute maximum ratings (Ta=25 °C)

Parameter	Symbol	Value	Unit
Reverse voltage	VR	5	V
Operating temperature	Topr	-25 to +70	°C
Storage temperature	Tstg	-25 to +70	°C

Electrical and optical characteristics (Ta=25 °C, per 1 element)

Parameter	Symbol	Condition	G7150-16			G7151-16			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	
Spectral response range	λ		-	0.9 to 1.7	-	-	0.9 to 1.7	-	μm
Peak sensitivity wavelength	λ_p		-	1.55	-	-	1.55	-	μm
Photo sensitivity	S	$\lambda=1.3 \mu\text{m}$		0.9	-		0.9	-	A/W
		$\lambda=1.55 \mu\text{m}$		0.95	-		0.95	-	
Dark current	Id	VR=1 V	-	5	25	-	0.2	1	nA
Cut-off frequency	fc	VR=1 V, RL=50 Ω $\lambda=1.3 \mu\text{m}$, -3 dB	-	30	-	-	300	-	MHz
Terminal capacitance	Ct	VR=1 V, f=1 MHz	-	100	-	-	10	-	pF
Shunt resistance	Rsh	VR=10 mV	-	100	-	-	1000	-	M Ω
Detectivity	D*	$\lambda=\lambda_p$	-	5×10^{12}	-	-	5×10^{12}	-	$\text{cm}\cdot\text{Hz}^{1/2}/\text{W}$
Noise equivalent power	NEP	$\lambda=\lambda_p$	-	2×10^{-14}	-	-	3×10^{-15}	-	$\text{W}/\text{Hz}^{1/2}$

Spectral response

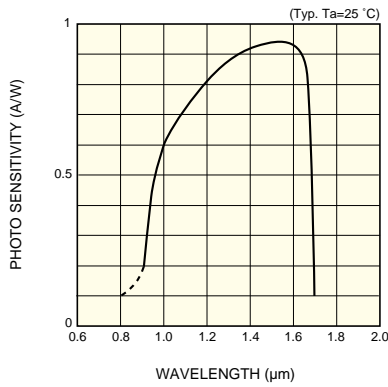
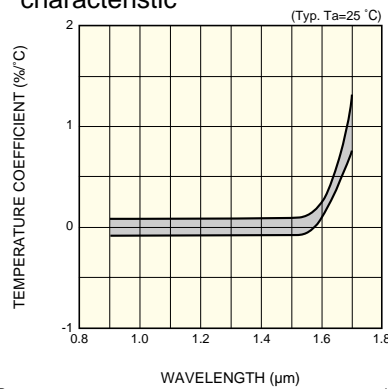
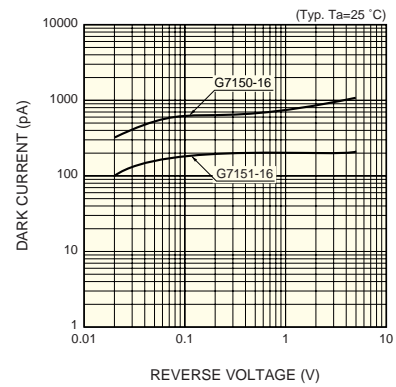


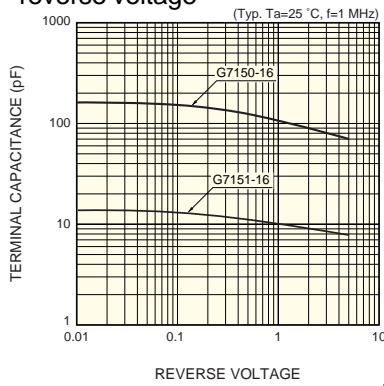
Photo sensitivity temperature characteristic



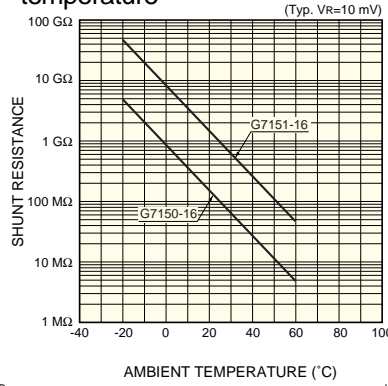
Dark current vs. reverse voltage



Terminal capacitance vs. reverse voltage

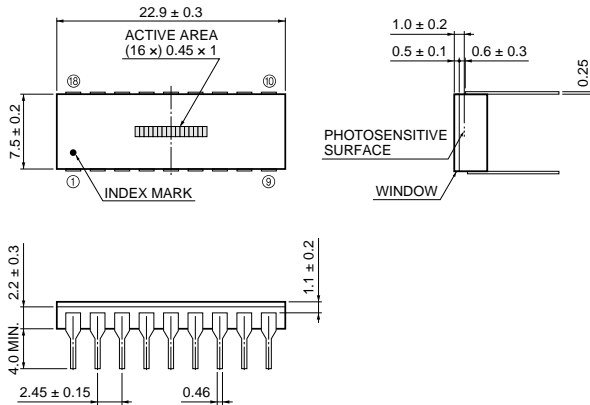


Shunt resistance vs. ambient temperature

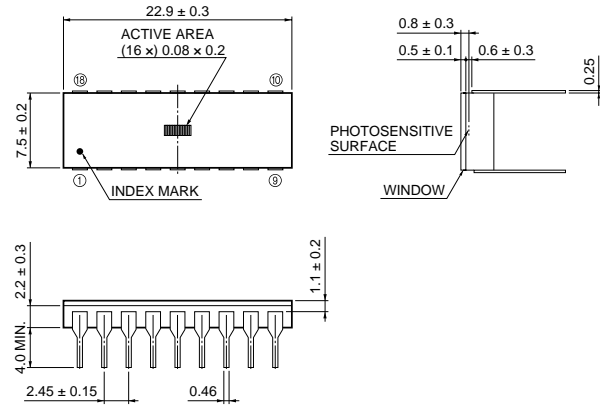


Dimensional outlines (unit: mm)

G7150-16



G7151-16



PIN No.	DETECTOR	PIN No.	DETECTOR	PIN No.	DETECTOR	PIN No.	DETECTOR
①	1	⑥	KC	⑪	14	⑯	6
②	3	⑦	11	⑫	12	⑰	4
③	5	⑧	13	⑬	KC	⑱	2
④	7	⑨	15	⑭	10		
⑤	9	⑩	16	⑮	8		

PIN No.	DETECTOR	PIN No.	DETECTOR	PIN No.	DETECTOR	PIN No.	DETECTOR
①	1	⑥	KC	⑪	14	⑯	6
②	3	⑦	11	⑫	12	⑰	4
③	5	⑧	13	⑬	KC	⑱	2
④	7	⑨	15	⑭	10		
⑤	9	⑩	16	⑮	8		

KIRDA0144EB

KIRDA0030ED

HAMAMATSU Information furnished by HAMAMATSU is believed to be reliable. However, no responsibility is assumed for possible inaccuracies or omissions. Specifications are subject to change without notice. No patent rights are granted to any of the circuits described herein. ©2003 Hamamatsu Photonics K.K.

HAMAMATSU PHOTONICS K.K., Solid State Division

1126-1 Ichino-cho, Hamamatsu City, 435-8558 Japan, Telephone: (81) 053-434-3311, Fax: (81) 053-434-5184, <http://www.hamamatsu.com>

U.S.A.: Hamamatsu Corporation: 360 Foothill Road, P.O.Box 6910, Bridgewater, N.J. 08807-0910, U.S.A., Telephone: (1) 908-231-0960, Fax: (1) 908-231-1218

Germany: Hamamatsu Photonics Deutschland GmbH: Arzbergerstr. 10, D-82211 Herrsching am Ammersee, Germany, Telephone: (49) 08152-3750, Fax: (49) 08152-2658

France: Hamamatsu Photonics France S.A.R.L.: 8, Rue du Saule Trapu, Parc du Moulin de Massy, 91882 Massy Cedex, France, Telephone: 33-(1) 69 53 71 00, Fax: 33-(1) 69 53 71 10

United Kingdom: Hamamatsu Photonics UK Limited: 2 Howard Court, 10 Tewin Road, Welwyn Garden City, Hertfordshire AL7 1BW, United Kingdom, Telephone: (44) 1707-294888, Fax: (44) 1707-325777

North Europe: Hamamatsu Photonics Norden AB: Smidesvägen 12, SE-171 41 Solna, Sweden, Telephone: (46) 8-509-031-00, Fax: (46) 8-509-031-01

Italy: Hamamatsu Photonics Italia S.R.L.: Strada della Moia, 1/E, 20020 Arese, (Milano), Italy, Telephone: (39) 02-935-81-733, Fax: (39) 02-935-81-741